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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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BT169 series Thyristors logic level Rev. 5 — 30 September 2011

Product data sheet

1. **Product profile**

1.1 General description

Passivated, sensitive gate thyristors in a SOT54 plastic package.

1.2 Features and benefits

Designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.3 Applications

General purpose switching and phase control applications.

1.4 Quick reference data

- V_{DRM} , $V_{RRM} \le 200 \text{ V (BT169B)}$
- V_{DRM}, V_{RRM} ≤ 400 V (BT169D)
- V_{DRM} , $V_{RRM} \le 600 \text{ V (BT169G)}$
- $I_{T(RMS)} \le 0.8 A$
- $I_{T(AV)} \le 0.5 A$
- $\blacksquare \quad I_{TSM} \leq 8 \ A$

Pinning information 2.

Table 1. Discrete pinning

| Pin | Description | Simplified outline | Symbol |
|-----|-------------|--------------------|-------------|
| 1 | anode (a) | | N 1 |
| 2 | gate (g) | | A 🖟 K G |
| 3 | cathode (k) | | G sym037 |
| | | SOT54 (TO-92) | |



3. Ordering information

Table 2. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BT169B | - | plastic single-ended leaded (through hole) package; 3 leads | SOT54 |
| BT169D | | | |
| BT169G | | | |

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--|---|--------------|------|------------------|
| V_{DRM}, V_{RRM} | repetitive peak off-state voltages | | | | |
| | BT169B | | <u>[1]</u> - | 200 | V |
| | BT169D | | <u>[1]</u> - | 400 | V |
| | BT169G | | <u>[1]</u> - | 600 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave; $T_{lead} \le 83 ^{\circ}C$; see Figure 1 | - | 0.5 | А |
| I _{T(RMS)} | RMS on-state current | all conduction angles; see <u>Figure 4</u> and <u>5</u> | - | 0.8 | Α |
| I _{TSM} | non-repetitive peak on-state current | half sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3 | | | |
| | | t = 10 ms | - | 8 | Α |
| | | t = 8.3 ms | - | 9 | Α |
| I ² t | I ² t for fusing | t = 10 ms | - | 0.32 | A ² s |
| dI _T /dt | repetitive rate of rise of on-state current after triggering | I_{TM} = 2 A; I_G = 10 mA; dI_G/dt = 100 mA/ μ s | - | 50 | A/μs |
| I _{GM} | peak gate current | | - | 1 | Α |
| V_{GM} | peak gate voltage | | - | 5 | V |
| V_{RGM} | peak reverse gate voltage | | - | 5 | V |
| P_{GM} | peak gate power | | - | 2 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.1 | W |
| T _{stg} | storage temperature | | -40 | +150 | °C |
| T _j | junction temperature | | - | 125 | °C |

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

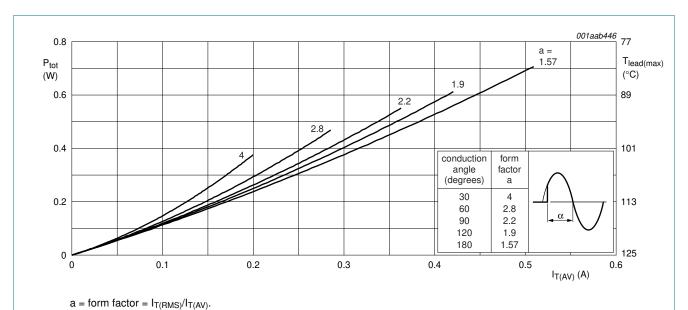
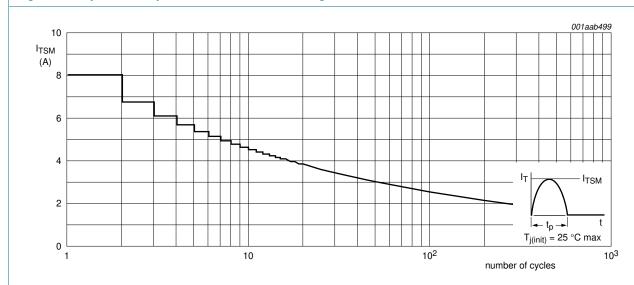


Fig 1. Total power dissipation as a function of average on-state current; maximum values.



f = 50 Hz.

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values.

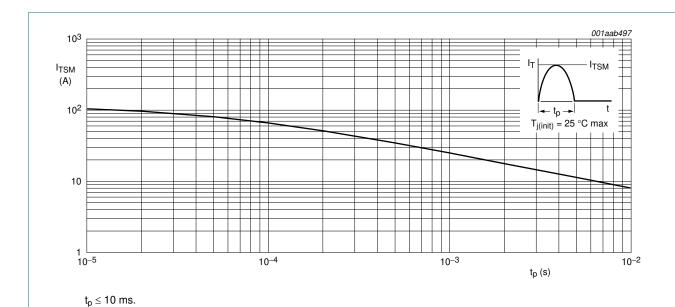


Fig 3. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values.

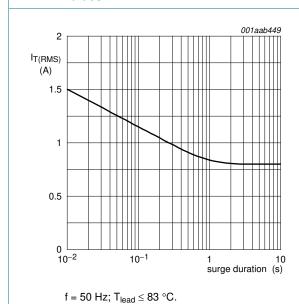
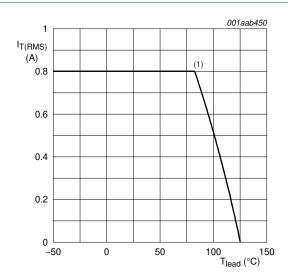


Fig 4. RMS on-state current as a function of surge duration for sinusoidal currents.



(1) $T_{lead} = 83 \, ^{\circ}C$.

Fig 5. RMS on-state current as a function of lead temperature; maximum values.

5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------|---|--|-----|-----|-----|------|
| $R_{th(j\text{-lead})}$ | thermal resistance from junction to lead | | - | - | 60 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | printed-circuit board mounted; lead length = 4 mm | - | 150 | - | K/W |

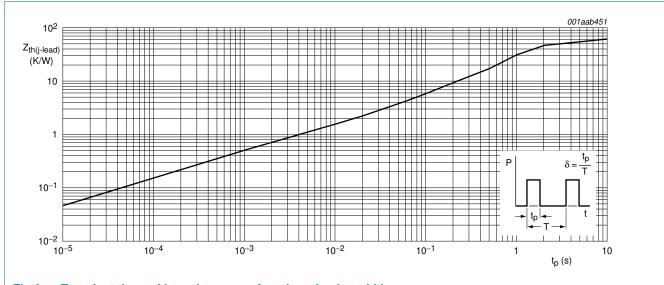


Fig 6. Transient thermal impedance as a function of pulse width.

6. Characteristics

Table 5. Characteristics

 $T_j = 25$ °C unless otherwise stated.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------|--|--|-----|------|-----|------|
| Static char | acteristics | | | | | |
| I _{GT} | gate trigger current $V_D = 12 \text{ V}; I_T = 10 \text{ mA};$ gate open circuit; see Figure 8 | | - | 50 | 200 | μΑ |
| IL | latching current | V_D = 12 V; I_{GT} = 0.5 mA; R_{GK} = 1 k Ω ; see <u>Figure 10</u> | - | 2 | 6 | mA |
| I _H | holding current | V_D = 12 V; I_{GT} = 0.5 mA; R_{GK} = 1 k Ω ; see <u>Figure 11</u> | - | 2 | 5 | mA |
| V_{T} | on-state voltage | I _T = 1.2 A | - | 1.25 | 1.7 | V |
| V_{GT} | gate trigger voltage | I _T = 10 mA; gate open circuit; see Figure 7 | | | | |
| | | V _D = 12 V | - | 0.5 | 0.8 | V |
| | | $V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$ | 0.2 | 0.3 | - | ٧ |
| I _D , I _R | off-state leakage current | $V_D = V_{DRM(max)}; V_R = V_{RRM(max)};$ $T_j = 125 ^{\circ}C; R_{GK} = 1 k\Omega$ | - | 0.05 | 0.1 | mA |
| Dynamic c | haracteristics | | | | | |
| dV _D /dt | critical rate of rise of off-state voltage | $V_{DM} = 67 \% V_{DRM(max)}; T_j = 125 °C;$ exponential waveform; see Figure 12 | | | | |
| | | $R_{GK} = 1 k\Omega$ | 500 | 800 | - | V/μs |
| | | gate open circuit | - | 25 | - | V/μs |
| t _{gt} | gate controlled turn-on time | $I_{TM} = 2 \text{ A}; V_D = V_{DRM(max)};$ $I_G = 10 \text{ mA}; dI_G/dt = 0.1 \text{ A}/\mu\text{s}$ | - | 2 | - | μS |
| t _q | circuit commuted turn-off time | $\begin{split} &V_D = 67 \;\% \; V_{DRM(max)}; \; T_j = 125 \; ^{\circ}C; \\ &I_{TM} = 1.6 \; A; \; V_R = 35 \; V; \\ &dI_{TM}/dt = 30 \; A/\mu s; \; dV_D/dt = 2 \; V/\mu s; \\ &R_{GK} = 1 \; k\Omega \end{split}$ | - | 100 | - | μЅ |

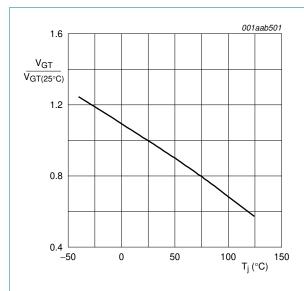


Fig 7. Normalized gate trigger voltage as a function of junction temperature.

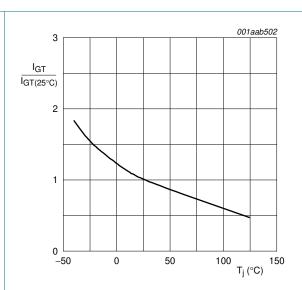
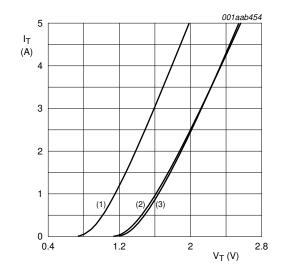


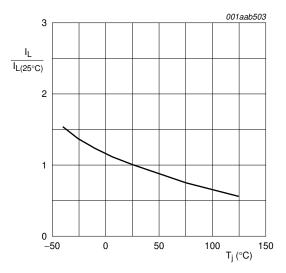
Fig 8. Normalized gate trigger current as a function junction temperature.



 $V_O = 1.067 \text{ V}.$ $R_S = 0.187 \Omega.$

- (1) $T_i = 125$ °C; typical values.
- (2) T_i = 125 °C; maximum values.
- (3) $T_j = 25$ °C; maximum values.

Fig 9. On-state current characteristics.



 $R_{GK} = 1 k\Omega$.

Fig 10. Normalized latching current as a function of junction temperature.

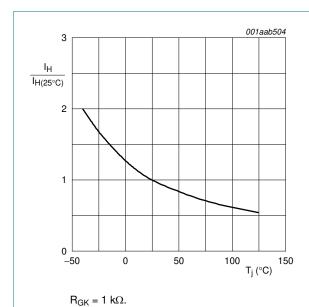
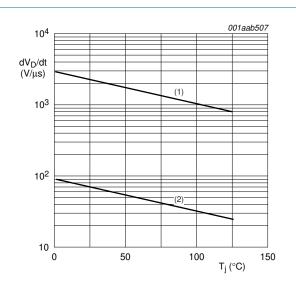


Fig 11. Normalized holding current as a function of junction temperature.



- (1) $R_{GK} = 1 k\Omega$.
- (2) Gate open circuit.

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values.

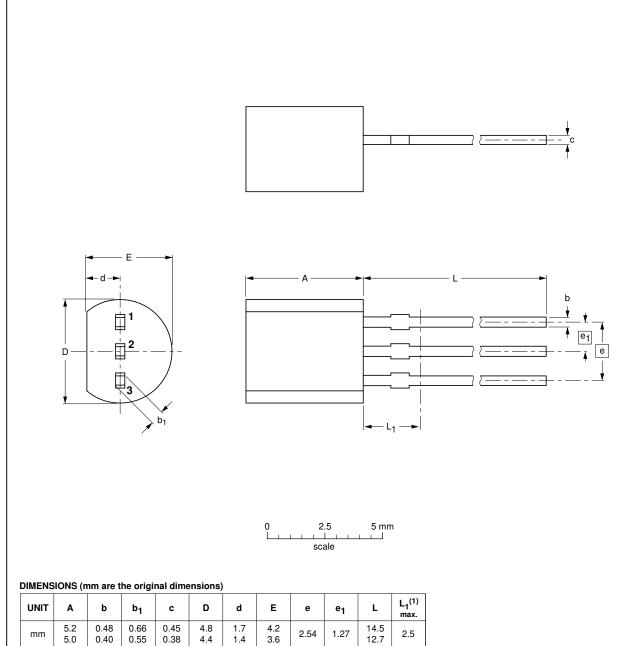
7. Package information

Epoxy meets requirements of UL94 V-0 at $\frac{1}{8}$ inch.

8. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



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1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE | | REFER | ENCES | | EUROPEAN PROJECTION | ISSUE DATE | |
|---------|-----|-------|--------|--|------------------------|---------------------------------|--|
| VERSION | IEC | JEDEC | JEITA | | | ISSUE DATE | |
| SOT54 | | TO-92 | SC-43A | | | 04 06 28 04-11-16 | |

Fig 13. Package outline SOT54 (TO-92).

BT169_SEF

9. Revision history

Table 6. Revision history

| Document ID | Release date | Data sheet status | Change notice | Order number | Supersedes | |
|------------------|---|---|---------------------|---------------------|--------------------|--|
| BT169_SERIES v.5 | 20110930 | Product data sheet | - | 9397 750 13512 | BT169_SERIES v.4 | |
| Modifications: | The format of this data sheet has been redesigned to comply with the new identity | | | | | |
| | · · | of NXP Semiconductors | | | | |
| | Legal texts | s have been adapted to t | he new company na | ame where appropr | iate. | |
| BT169_SERIES v.4 | 20040823 | Product data sheet | - | 9397 750 13512 | BT169_SERIES v.3 | |
| Modifications: | | t of this data sheet has b n standard of Philips Sen | | comply with the nev | v presentation and | |
| | Section 1. | 4 "Quick reference data": | BT169E obsolete, | removed from list. | | |
| | Table 2 "O | ordering information": BT1 | 169E obsolete, remo | oved from table. | | |
| | Table 3 "Li | imiting values": BT169E | obsolete, removed f | rom table. | | |
| BT169_SERIES v.3 | 20010902 | Product specification | - | not applicable | BT169_SERIES v.2 | |
| BT169_SERIES v.2 | 20010901 | Product specification | - | not applicable | BT169_SERIES v.1 | |
| BT169_SERIES v.1 | 19970901 | Product specification | - | not applicable | - | |
| | | | | | | |

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
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BT169 series

Thyristor logic level

12. Contents

| 1 | Product profile |
|------|---------------------------|
| 1.1 | General description |
| 1.2 | Features and benefits |
| 1.3 | Applications |
| 1.4 | Quick reference data 1 |
| 2 | Pinning information 1 |
| 3 | Ordering information 2 |
| 4 | Limiting values |
| 5 | Thermal characteristics 5 |
| 6 | Characteristics 6 |
| 7 | Package information 8 |
| 8 | Package outline 9 |
| 9 | Revision history |
| 10 | Legal information |
| 10.1 | Data sheet status |
| 10.2 | Definitions |
| 10.3 | Disclaimers |
| 10.4 | Trademarks |
| 11 | Contact information 12 |
| 12 | Contents |

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